Document Number: MMRF1007H
Rev. 0, 12/2013

RoHS

RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

MMRF1007HR5
MMRF1007HSR5

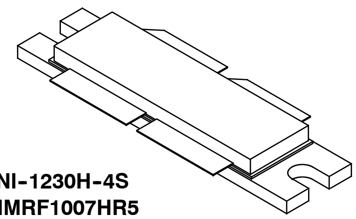
RF power transistors designed for applications operating at frequencies from 900 to 1215 MHz. These devices are suitable for use in defense and commercial pulse applications, such as IFF and DME.

- Typical Pulse Performance: V_{DD} = 50 Vdc, I_{DQ} = 150 mA, P_{out} = 1000 W Peak (100 W Avg.), f = 1030 MHz, Pulse Width = 128 μsec, Duty Cycle = 10%
  Power Gain — 20 dB
  Drain Efficiency — 56%
- Capable of Handling 5:1 VSWR, @ 50 Vdc, 1030 MHz, 1000 W Peak Power

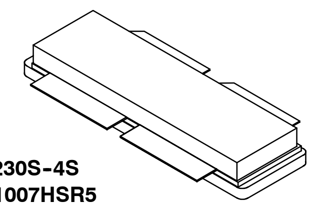
Features

- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 50 V_{DD} Operation
- Integrated ESD Protection
- Designed for Push-Pull Operation
- Greater Negative Gate-Source Voltage Range for Improved Class C Operation
- In Tape and Reel. R5 Suffix = 50 Units, 56 mm Tape Width, 13-inch Reel.

965-1215 MHz, 1000 W, 50 V
LATERAL N-CHANNEL
BROADBAND
RF POWER MOSFETs

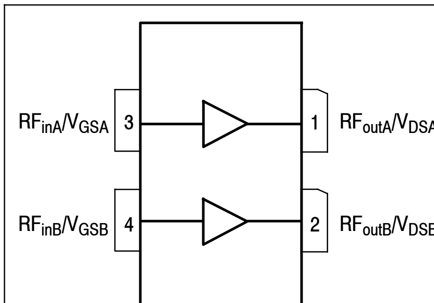


NI-1230H-4S
MMRF1007HR5



NI-1230S-4S
MMRF1007HSR5

PARTS ARE PUSH-PULL



(Top View)

Figure 1. Pin Connections

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +110	Vdc
Gate-Source Voltage	V_{GS}	-6.0, +10	Vdc
Storage Temperature Range	T_{stg}	- 65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature (1)	T_J	225	°C

1. Continuous use at maximum temperature will affect MTTF.

freescale

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (1)	Unit
Thermal Resistance, Junction to Case Case Temperature 67°C, 1000 W Peak, 128 μsec Pulse Width, 10% Duty Cycle, 50 Vdc, I_{DQ} = 150 mA Case Temperature 62°C, Mode-S Pulse Train, 80 Pulses of 32 μsec On, 18 μsec Off, Repeated Every 40 msec, 6.4% Overall Duty Cycle, 50 Vdc, I_{DQ} = 150 mA	$Z_{\theta JC}$	 0.02 0.07	°C/W

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	1B
Machine Model (per EIA/JESD22-A115)	B
Charge Device Model (per JESD22-C101)	IV

Table 4. Electrical Characteristics (T_A = 25°C unless otherwise noted)

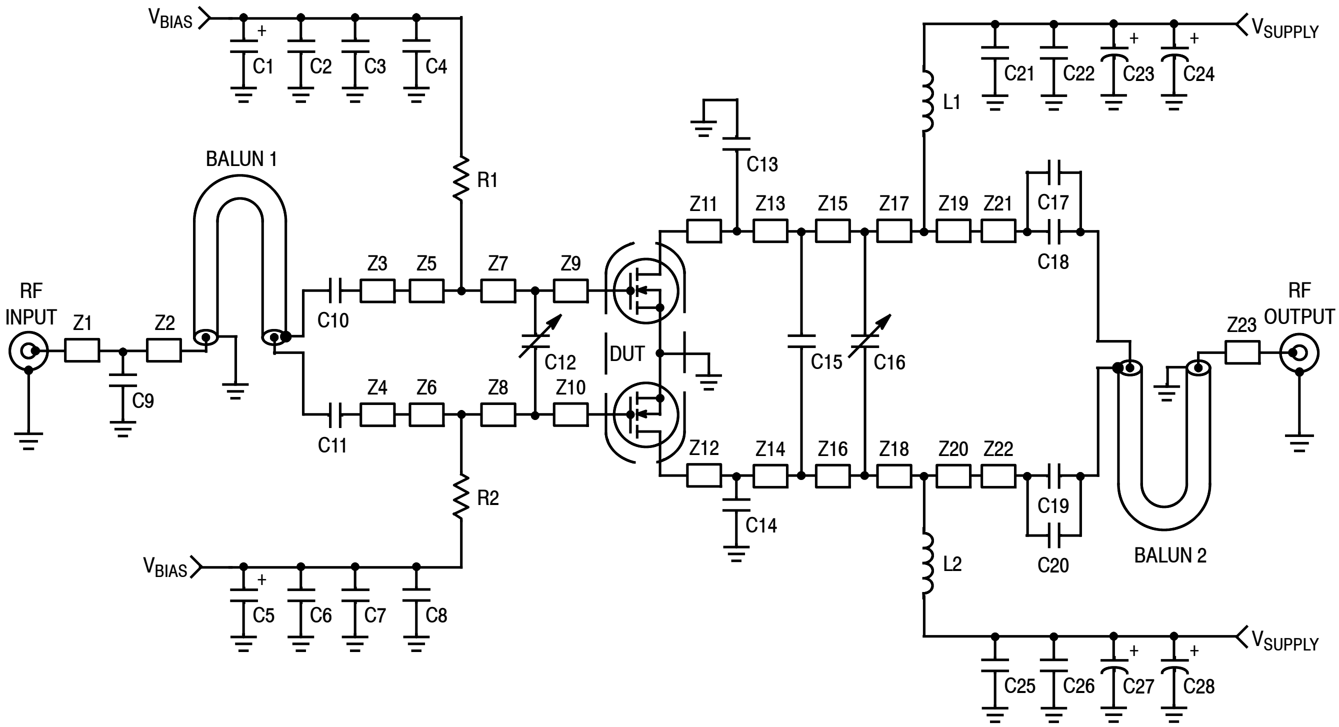
Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics (2)					
Gate-Source Leakage Current (V_{GS} = 5 Vdc, V_{DS} = 0 Vdc)	I_{GSS}	—	—	10	μAdc
Drain-Source Breakdown Voltage (V_{GS} = 0 Vdc, I_D = 165 mA)	$V_{(BR)DSS}$	110	—	—	Vdc
Zero Gate Voltage Drain Leakage Current (V_{DS} = 50 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current (V_{DS} = 100 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	100	μAdc
On Characteristics					
Gate Threshold Voltage (2) (V_{DS} = 10 Vdc, I_D = 1000 μAdc)	$V_{GS(th)}$	0.9	1.6	2.4	Vdc
Gate Quiescent Voltage (3) (V_{DD} = 50 Vdc, I_D = 150 mAdc, Measured in Functional Test)	$V_{GS(Q)}$	1.5	2.2	3	Vdc
Drain-Source On-Voltage (2) (V_{GS} = 10 Vdc, I_D = 2.7 Adc)	$V_{DS(on)}$	—	0.15	—	Vdc
Dynamic Characteristics (2)					
Reverse Transfer Capacitance (V_{DS} = 50 Vdc ± 30 mV(rms)ac @ 1 MHz, V_{GS} = 0 Vdc)	C_{rss}	—	1.27	—	pF
Output Capacitance (V_{DS} = 50 Vdc ± 30 mV(rms)ac @ 1 MHz, V_{GS} = 0 Vdc)	C_{oss}	—	86.7	—	pF
Input Capacitance (V_{DS} = 50 Vdc, V_{GS} = 0 Vdc ± 30 mV(rms)ac @ 1 MHz)	C_{iss}	—	539	—	pF
Functional Tests (3) (In Freescale Test Fixture, 50 ohm system) V_{DD} = 50 Vdc, I_{DQ} = 150 mA, P_{out} = 1000 W Peak (100 W Avg.), f = 1030 MHz, 128 μsec Pulse Width, 10% Duty Cycle					
Power Gain	G_{ps}	19	20	22	dB
Drain Efficiency	η_D	54	56	—	%
Input Return Loss	IRL	—	-23	-9	dB

1. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers.* Go to http://www.freescale.com/rf. Select Documentation/Application Notes - AN1955.
2. Each side of device measured separately.
3. Measurement made with device in push-pull configuration.

(continued)

Table 4. Electrical Characteristics (T_A = 25°C unless otherwise noted) **(continued)**

Characteristic	Symbol	Min	Typ	Max	Unit
Typical Performance — 1030 MHz (In Freescale 1030 MHz Test Fixture, 50 ohm system) V_{DD} = 50 Vdc, I_{DQ} = 150 mA, P_{out} = 1000 W Peak (100 W Avg.), f = 1030 MHz, Mode-S Pulse Train, 80 Pulses of 32 μsec On, 18 μsec Off, Repeated Every 40 msec, 6.4% Overall Duty Cycle					
Power Gain	G_{ps}	—	19.8	—	dB
Drain Efficiency	η_D	—	59.0	—	%
Burst Droop	BD_{rp}	—	0.21	—	dB
Typical Performance — 1090 MHz (In Freescale 1090 MHz Test Fixture, 50 ohm system) V_{DD} = 50 Vdc, I_{DQ} = 150 mA, P_{out} = 1000 W Peak (100 W Avg.), f = 1090 MHz, 128 μsec Pulse Width, 10% Duty Cycle					
Power Gain	G_{ps}	—	21.4	—	dB
Drain Efficiency	η_D	—	56.3	—	%
Input Return Loss	IRL	—	-25.3	—	dB



Z1	0.140″ x 0.083″	Z13, Z14	0.143″ x 0.631″
Z2	0.300″ x 0.083″	Z15, Z16	0.135″ x 0.631″
Z3, Z4	0.746″ x 0.220″	Z17, Z18	0.102″ x 0.632″
Z5, Z6	0.075″ x 0.631″	Z19, Z20	0.130″ x 0.631″
Z7, Z8	0.329″ x 0.631″	Z21, Z22	0.736″ x 0.215″
Z9, Z10	0.326″ x 0.631″	Z23	0.410″ x 0.083″
Z11, Z12	0.240″ x 0.631″	PCB	Arlon CuClad 250GX-0300-55-22, 0.030″, ε_r = 2.55

Figure 2. MMRF1007HR5(HSR5) Test Circuit Schematic

Table 5. MMRF1007HR5(HSR5) Test Circuit Component Designations and Values

Part	Description	Manufacturer	Part Number
Balun 1, 2	Balun Anaren	3A412	Anaren
C1, C5	22 μF, 25 V Tantalum Capacitors	TPSD226M025R	AVX
C2, C6	2.2 μF, 50 V Chip Capacitors	C1825C225J5RAC	Kemet
C3, C7	0.22 μF, 100 V Chip Capacitors	C1210C224K1RAC	Kemet
C4, C8, C17, C18, C19, C20, C21, C25	36 pF Chip Capacitors	ATC100B360JT500XT	ATC
C9	1.0 pF Chip Capacitor	ATC100B1R0CT500XT	ATC
C12, C16	0.8-8.0 pF Variable Capacitors	27291SL	Johanson
C10, C11, C13, C14, C15	5.1 pF Chip Capacitors	ATC100B5R1CT500XT	ATC
C22, C26	0.022 μF, 100 V Chip Capacitors	C1825C223K1GAC	Kemet
C23, C24, C27, C28	470 μF, 63 V Electrolytic Capacitors	MCGPR63V477M13X26-RH	Multicomp
L1, L2	Inductors 3 Turn	GA3094-AL	Coilcraft
R1, R2	1000 Ω, 1/3 W Chip Resistors	CRCW12101001FKEA	Vishay

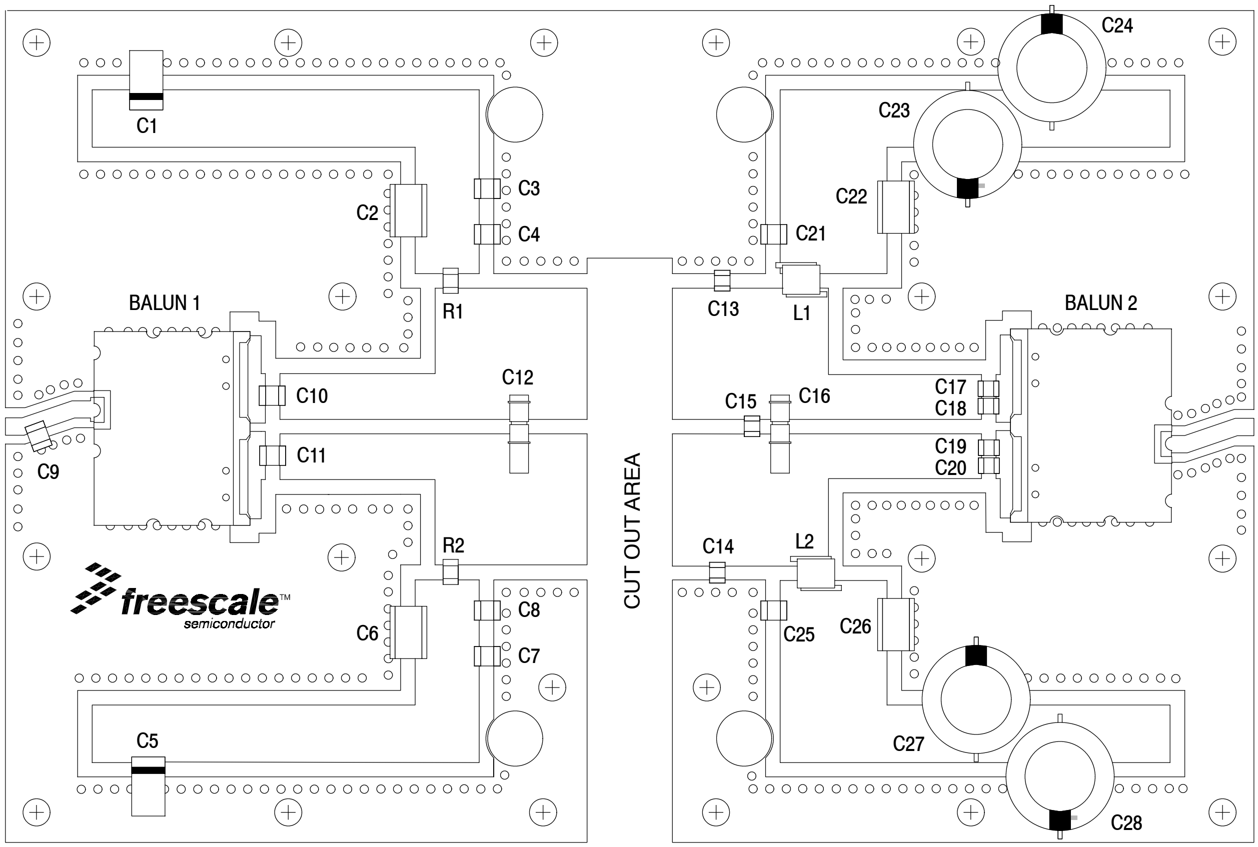
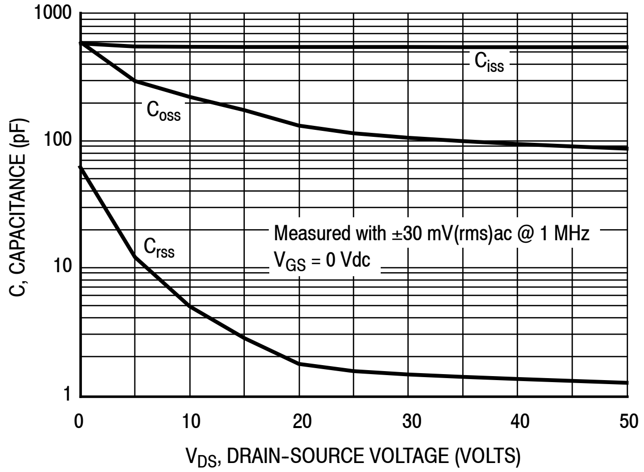


Figure 3. MMRF1007HR5(HSR5) Test Circuit Component Layout



Note: Each side of device measured separately.

Figure 4. Capacitance versus Drain-Source Voltage

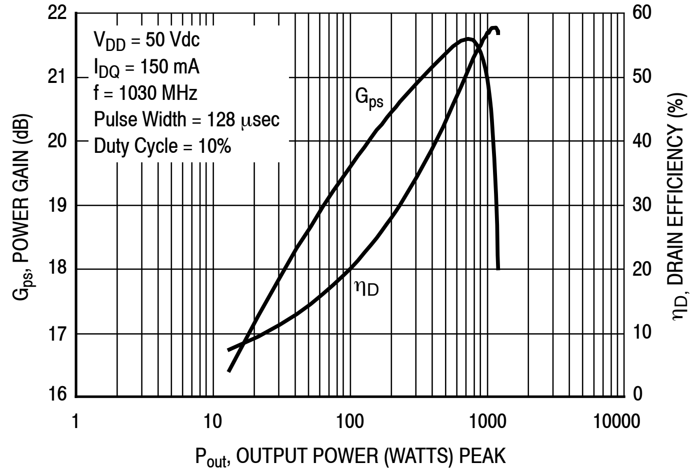


Figure 5. Power Gain and Drain Efficiency versus Output Power

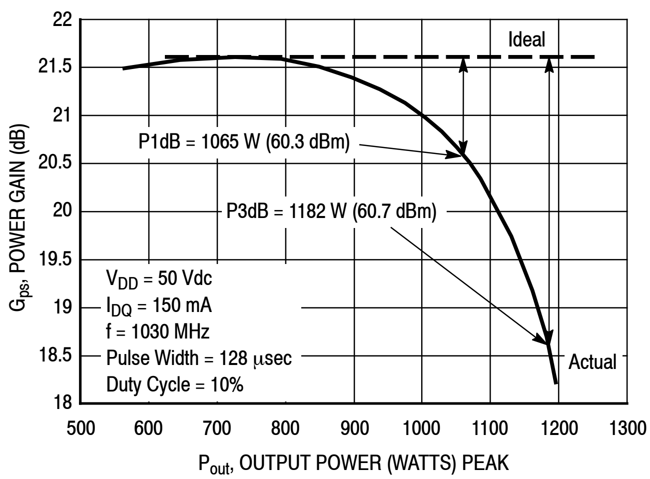


Figure 6. Power Gain versus Output Power

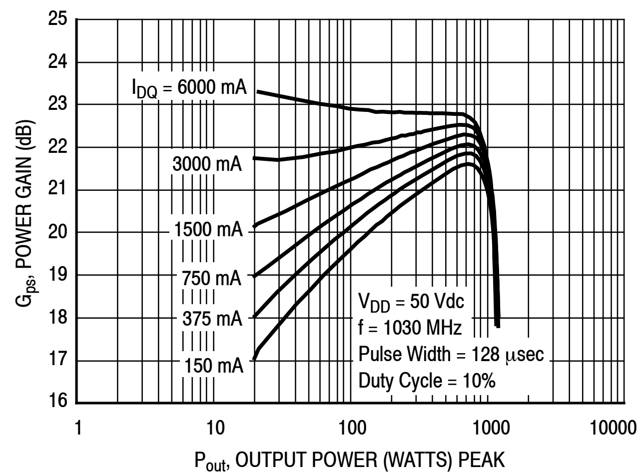


Figure 7. Power Gain versus Output Power

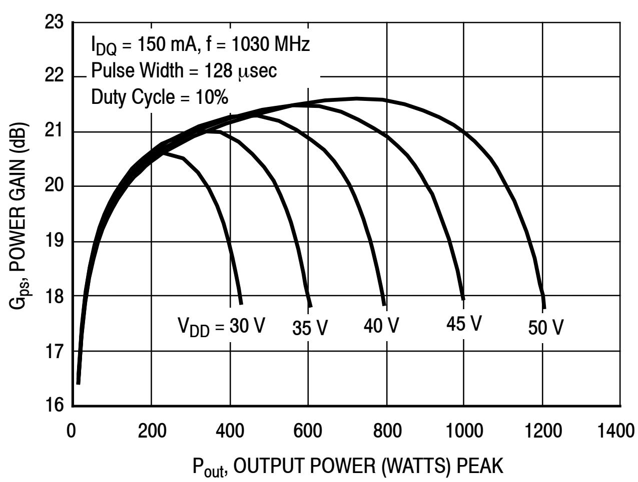


Figure 8. Power Gain versus Output Power

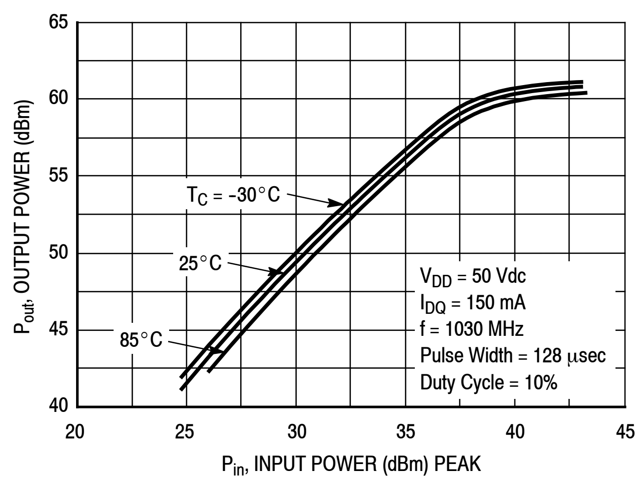


Figure 9. Output Power versus Input Power

TYPICAL CHARACTERISTICS

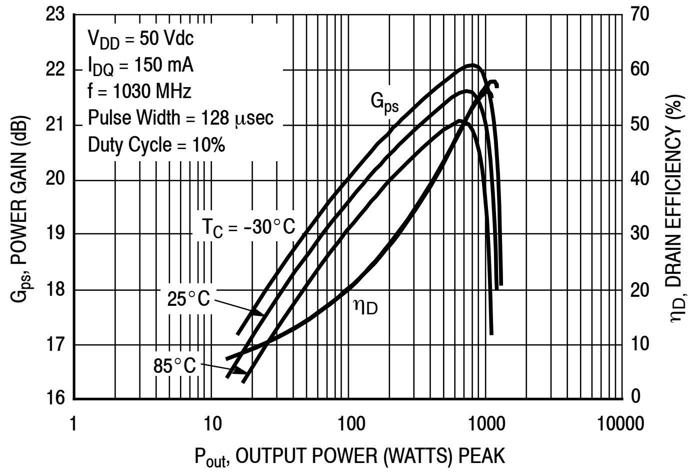
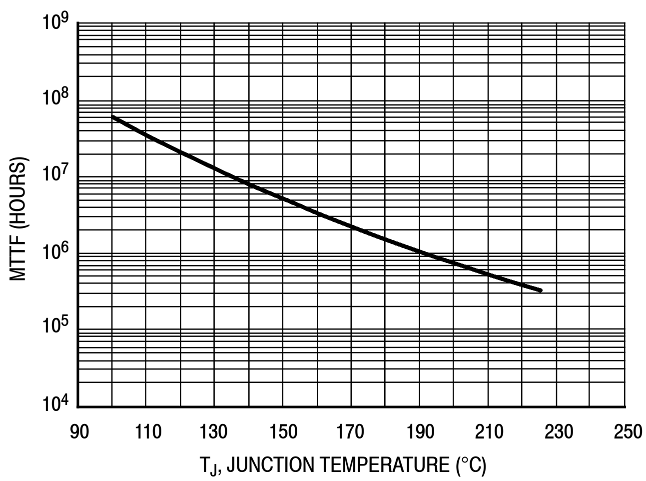


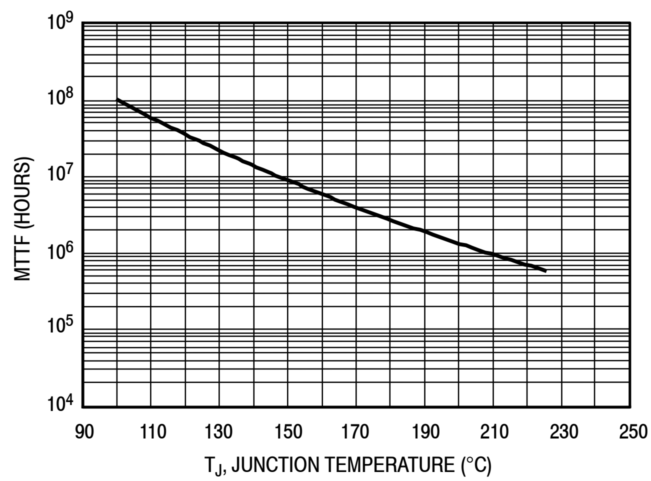
Figure 10. Power Gain and Drain Efficiency versus Output Power



This above graph displays calculated MTTF in hours when the device is operated at V_{DD} = 50 Vdc, P_{out} = 1000 W Peak, Pulse Width = 128 μsec, Duty Cycle = 10%, and η_D = 56%.

MTTF calculator available at http://www.freescale.com/rf. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.

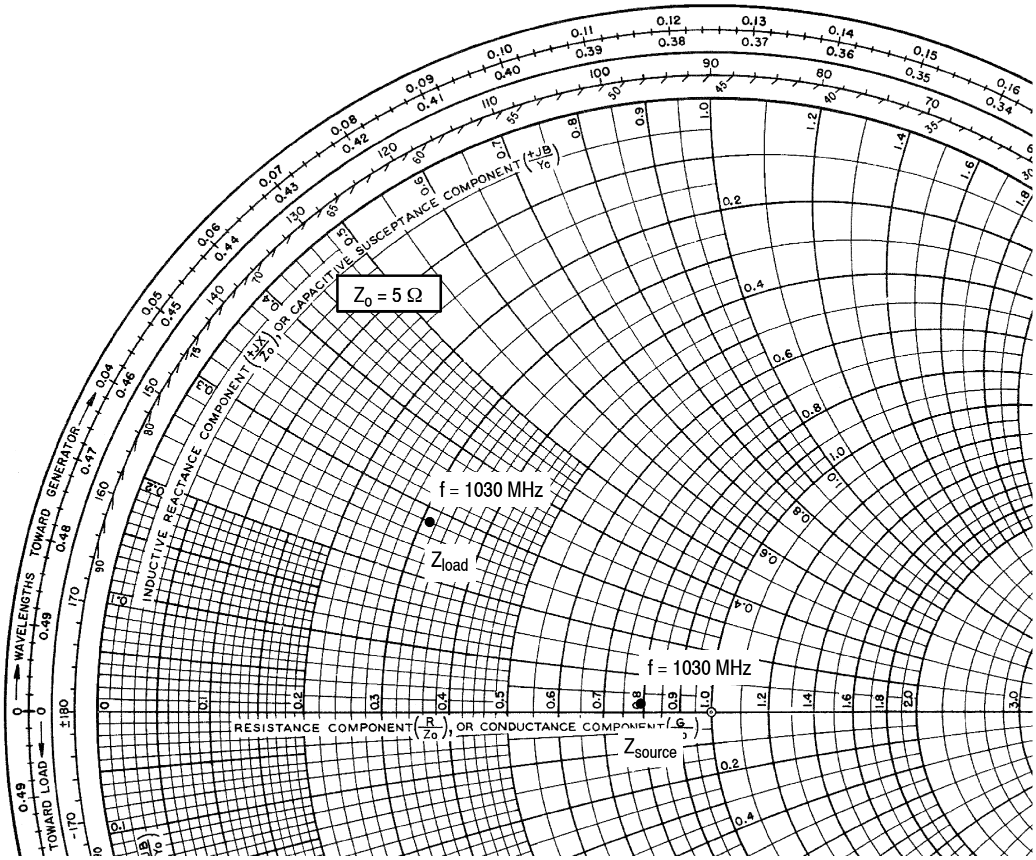
Figure 11. MTTF versus Junction Temperature - 128 μsec, 10% Duty Cycle



This above graph displays calculated MTTF in hours when the device is operated at V_{DD} = 50 Vdc, P_{out} = 1000 W Peak, Mode-S Pulse Train, Pulse Width = 32 μsec, Duty Cycle = 6.4%, and η_D = 59%.

MTTF calculator available at http://www.freescale.com/rf. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.

Figure 12. MTTF versus Junction Temperature - Mode-S



V_{DD} = 50 Vdc, I_{DQ} = 150 mA, P_{out} = 1000 W Peak

f MHz	Z_{source} Ω	Z_{load} Ω
1030	3.93 + j0.09	1.54 + j1.42

Z_{source} = Test circuit impedance as measured from gate to gate, balanced configuration.

Z_{load} = Test circuit impedance as measured from drain to drain, balanced configuration.

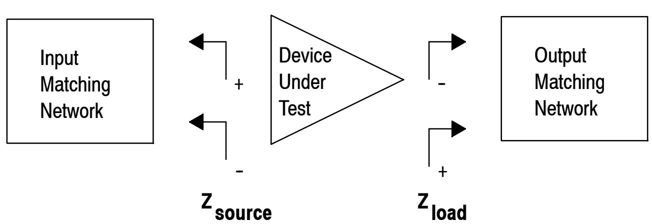


Figure 13. Series Equivalent Source and Load Impedance

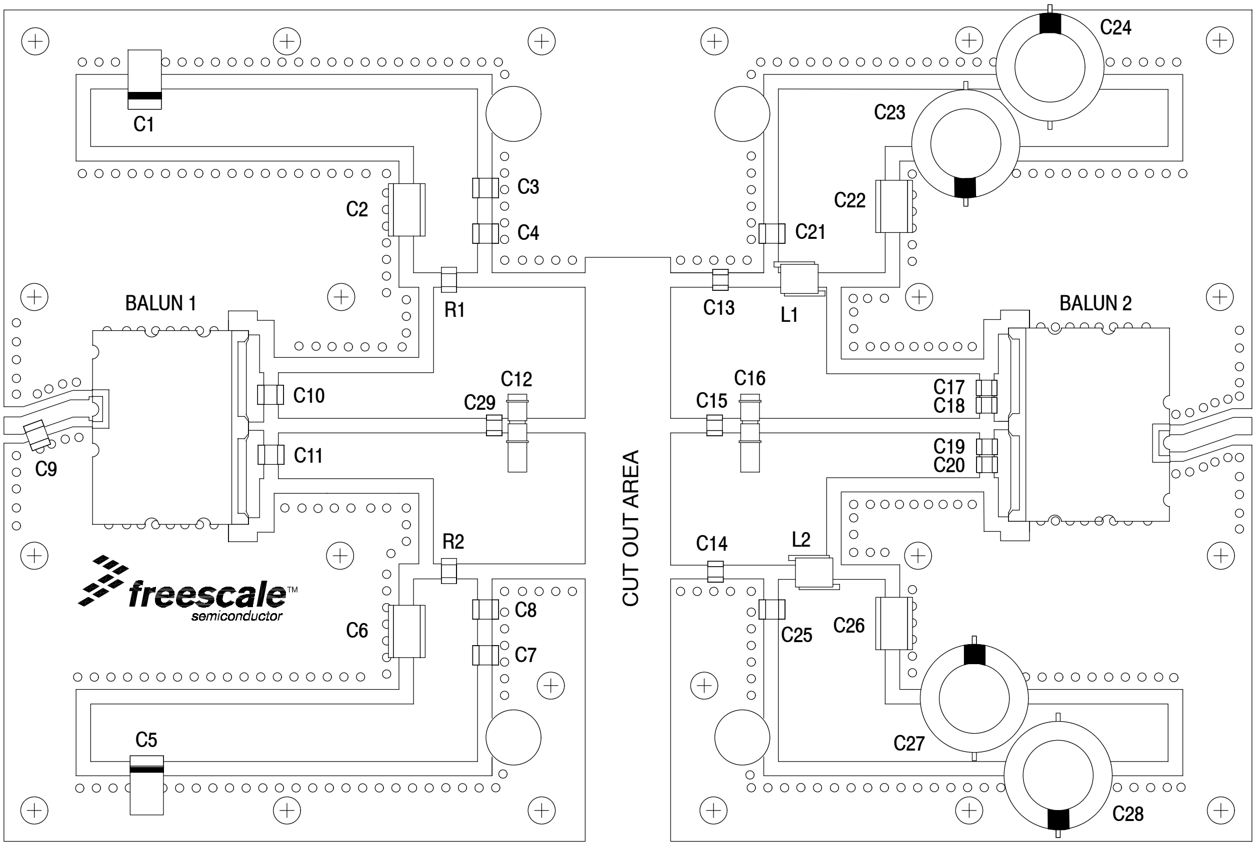


Figure 14. MMRF1007HR5(HSR5) Test Circuit Component Layout — 1090 MHz

Table 6. MMRF1007HR5(HSR5) Test Circuit Component Designations and Values — 1090 MHz

Part	Description	Manufacturer	Part Number
Balun 1, 2	Balun Anaren	3A412	Anaren
C1, C5	22 μF, 25 V Tantalum Capacitors	TPSD226M025R0200	AVX
C2, C6	2.2 μF, 50 V 1825 Chip Capacitors	C1825C225J5RAC-TU	Kemet
C3, C7	0.22 μF, 100 V Chip Capacitors	C1210C224K1RAC-TU	Kemet
C4, C8, C17, C18, C19, C20, C21, C25	36 pF Chip Capacitors	ATC100B360JT500XT	ATC
C9	1.0 pF Chip Capacitor	ATC100B1R0BT500XT	ATC
C12, C16	0.8-8.0 pF Variable Capacitors	27291SL	Johanson
C10, C11, C13, C14, C15, C29	5.1 pF Chip Capacitors	ATC100B5R1CT500XT	ATC
C22, C26	0.022 μF, 100 V Chip Capacitors	C1825C223K1GAC	Kemet
C23, C24, C27, C28	470 μF, 63 V Electrolytic Capacitors	MCGPR63V477M13X26-RH	Multicomp
L1, L2	Inductors 3 Turn	GA3094-ALC	Coilcraft
R1, R2	1000 Ω, 1/4 W Chip Resistors	CRCW12061K00FKEA	Vishay
PCB	CuClad, 0.030″, ε_r = 2.55	250GX-0300-55-22	Arlon

TYPICAL CHARACTERISTICS — 1090 MHZ

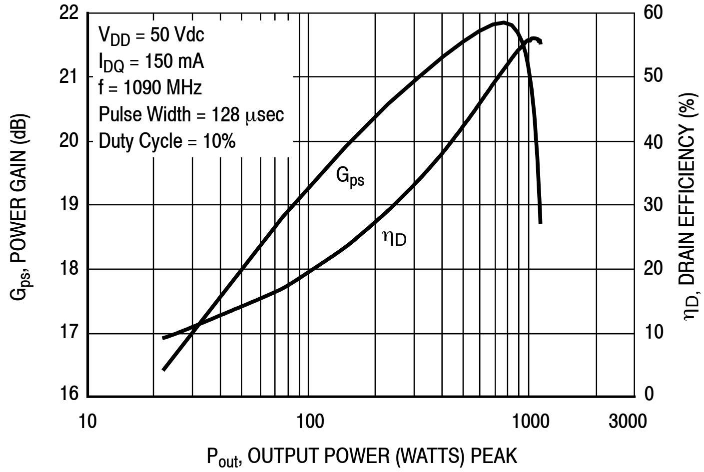
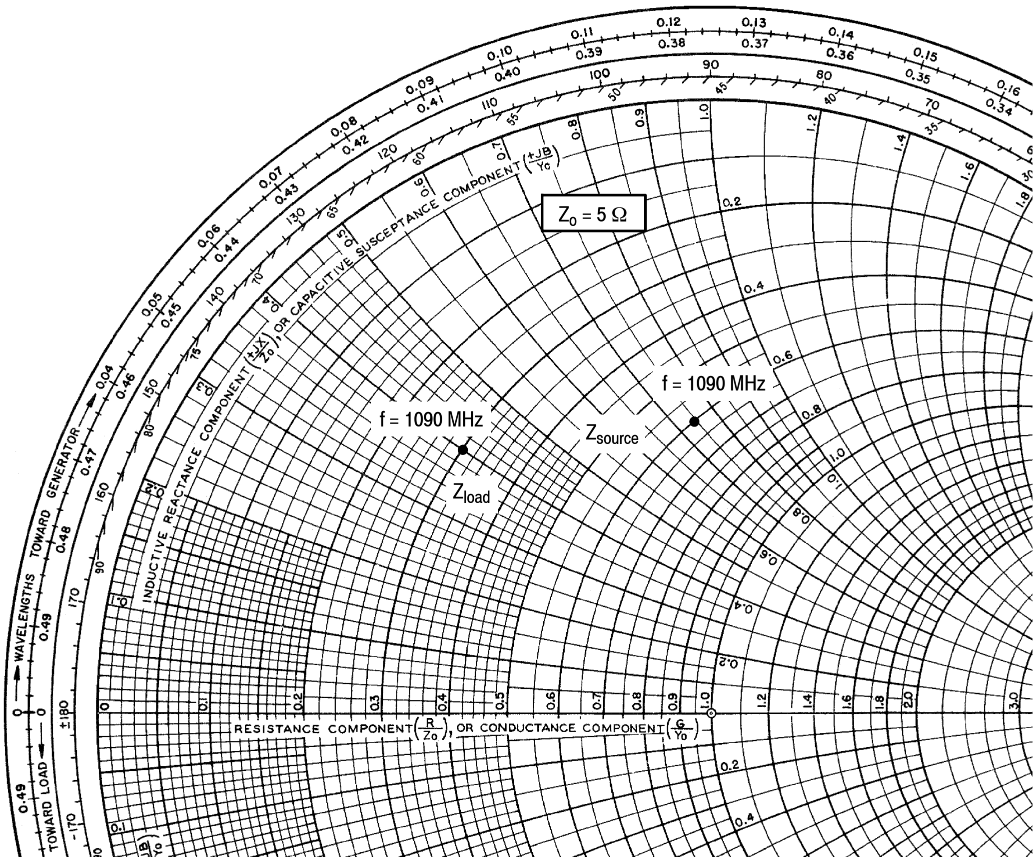


Figure 15. Power Gain and Drain Efficiency versus Output Power



V_{DD} = 50 Vdc, I_{DQ} = 150 mA, P_{out} = 1000 W Peak

f MHz	Z_{source} Ω	Z_{load} Ω
1090	2.98 + j3.68	1.51 + j2.02

Z_{source} = Test circuit impedance as measured from gate to gate, balanced configuration.

Z_{load} = Test circuit impedance as measured from drain to drain, balanced configuration.

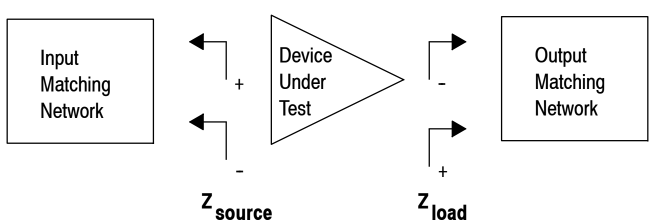
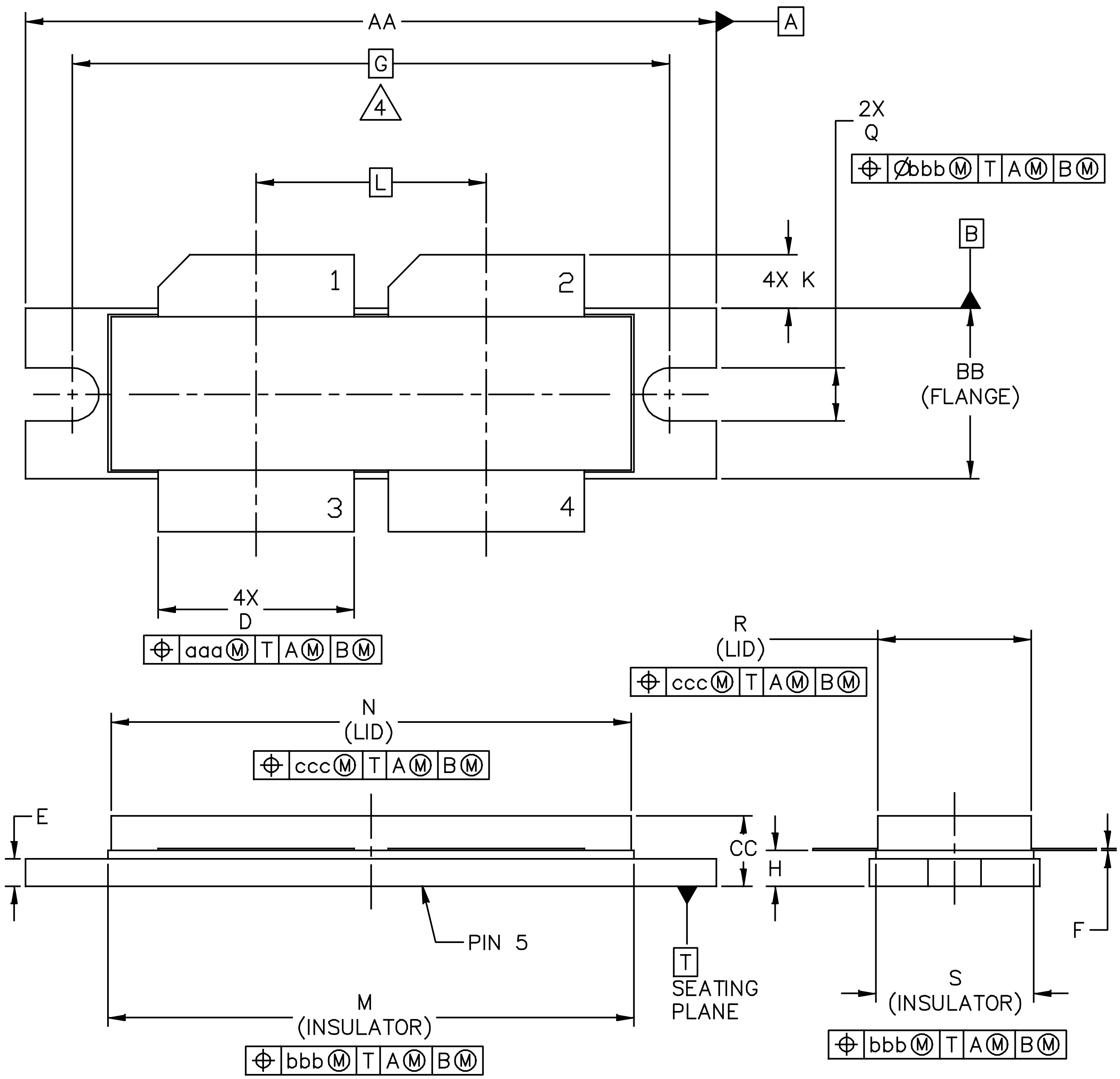


Figure 16. Series Equivalent Source and Load Impedance — 1090 MHz

PACKAGE DIMENSIONS



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TITLE: NI–1230–4H	DOCUMENT NO: 98ASB16977C	REV: F
	STANDARD: NON–JEDEC	
	28 FEB 2013	

NOTES:

1. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.

2. CONTROLLING DIMENSION: INCH

3. DIMENSION H IS MEASURED .030 INCH (0.762 MM) AWAY FROM PACKAGE BODY.

4. RECOMMENDED BOLT CENTER DIMENSION OF 1.52 INCH (38.61 MM) BASED ON M3 SCREW.

DIM	INCH MIN	INCH MAX	MILLIMETER MIN	MILLIMETER MAX	DIM	INCH MIN	INCH MAX	MILLIMETER MIN	MILLIMETER MAX
AA	1.615	1.625	41.02	41.28	N	1.218	1.242	30.94	31.55
BB	.395	.405	10.03	10.29	Q	.120	.130	3.05	3.30
CC	.170	.190	4.32	4.83	R	.355	.365	9.02	9.27
D	.455	.465	11.56	11.81	S	.365	.375	9.27	9.53
E	.062	.066	1.57	1.68					
F	.004	.007	0.10	0.18					
G	1.400 BSC		35.56 BSC		aaa	.013		0.33	
H	.082	.090	2.08	2.29	bbb	.010		0.25	
K	.117	.137	2.97	3.48	ccc	.020		0.51	
L	.540 BSC		13.72 BSC						
M	1.219	1.241	30.96	31.52					

	MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE
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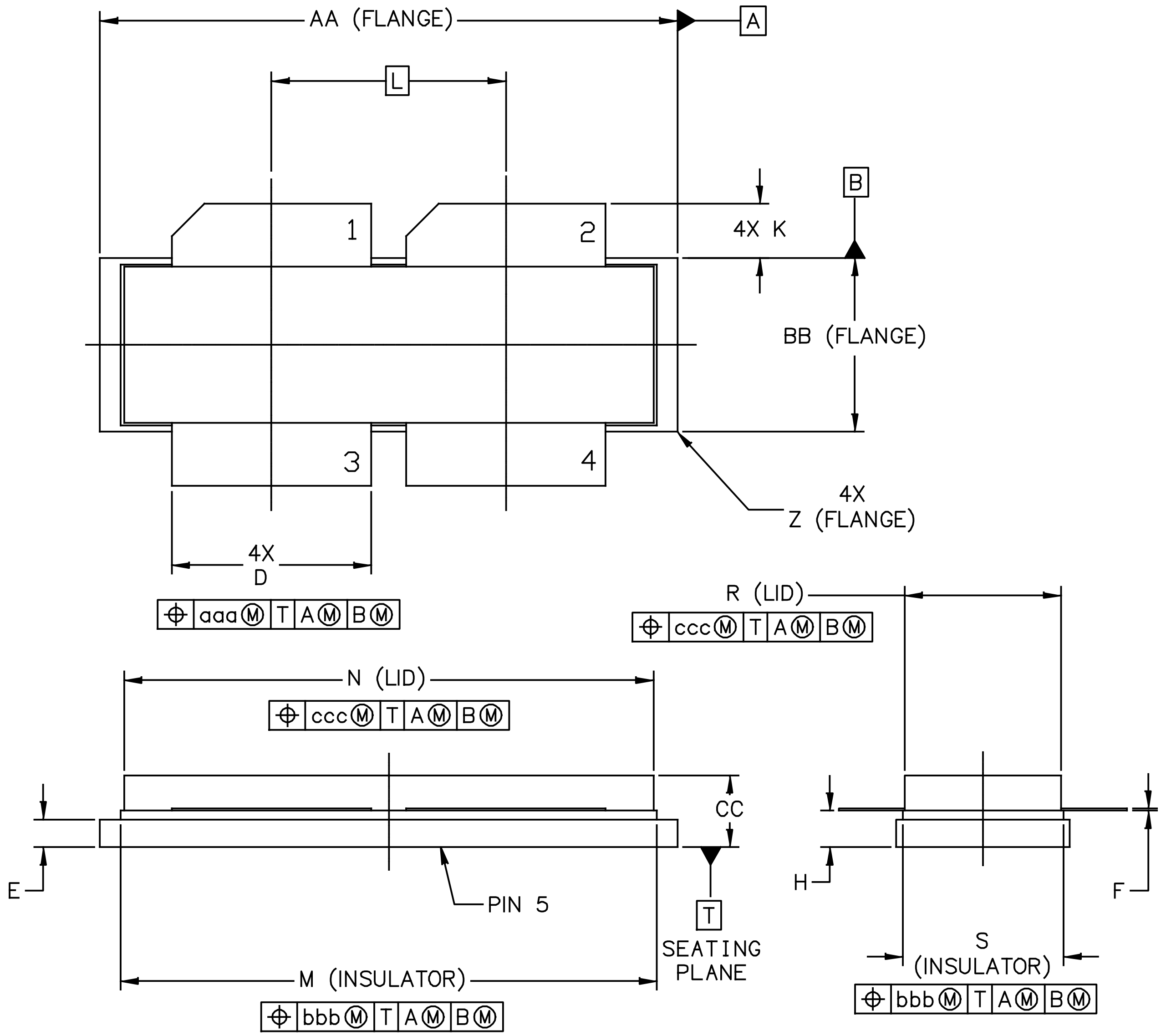
	STANDARD: NON-JEDEC	
	28 FEB 2013	



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TITLE: NI–1230–4S	DOCUMENT NO: 98ARB18247C	REV: G
	STANDARD: NON–JEDEC	
	01 MAR 2013	

NOTES:

1. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M−1994.

2. CONTROLLING DIMENSION: INCH

3. DIMENSION H IS MEASURED .030 INCH (0.762 MM) AWAY FROM PACKAGE BODY

DIM	INCHES		MILLIMETERS		DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
AA	1.265	1.275	32.13	32.39	R	.355	.365	9.02	9.27
BB	.395	.405	10.03	10.29	S	.365	.375	9.27	9.53
CC	.170	.190	4.32	4.83	Z	R.000	R.040	R0.00	R1.02
D	.455	.465	11.56	11.81					
E	.062	.066	1.57	1.68	aaa	.013		0.33	
F	.004	.007	0.10	0.18	bbb	.010		0.25	
H	.082	.090	2.08	2.29	ccc	.020		0.51	
K	.117	.137	2.97	3.48					
L	.540 BSC		13.72 BSC						
M	1.219	1.241	30.96	31.52					
N	1.218	1.242	30.94	31.55					

	MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE
TITLE: NI−1230−4S	DOCUMENT NO: 98ARB18247C	REV: G
	STANDARD: NON−JEDEC	
		01 MAR 2013

PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	Dec. 2013	• Initial Release of Data Sheet

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Rev. 0, 12/2013